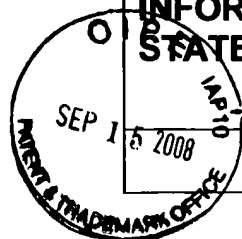


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Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

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	WO 00/03429A1	20-Jan-00	PCT				X
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Examiner Signature		Date Considered	
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